Silicon PNP Power Transistors 2SA1758

DESCRIPTION

- With TO-220Fa package
- Low collector saturation voltage
- Wide area of safe operation

APPLICATIONS

- For power switching applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base

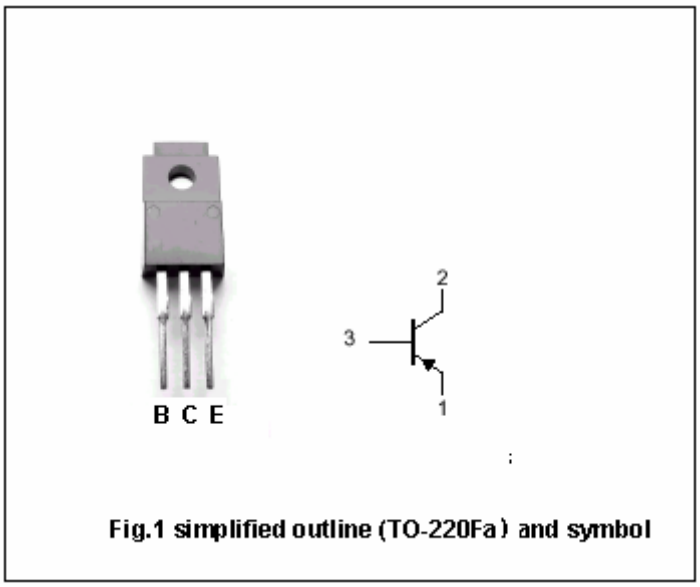


Fig.1 simplified outline (TO-220Fa) and symbol

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-100	V
V_{CEO}	Collector-emitter voltage	Open base	-60	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-12	A
P_C	Collector power dissipation	T_C=25℃	30	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-1mA ,I_B=0	-60			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=-50μA ,I_C=0	-5			V
$V_{CEsat-1}$	Collector-emitter saturation voltage	I_C=-6A; I_B=-0.3A			-0.3	V
$V_{CEsat-2}$	Collector-emitter saturation voltage	I_C=-8A; I_B=-0.4A			-0.5	V
$V_{BEsat-1}$	Base-emitter saturation voltage	I_C=-6A; I_B=-0.3A			-1.2	V
$V_{BEsat-2}$	Base-emitter saturation voltage	I_C=-8A; I_B=-0.4A			-1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=-100V; I_E=0			-10	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-5V; I_C=0			-10	μA
h_{FE}	DC current gain	I_C=-2A ; V_{CE}=-2V	60		320	
f_T	Transition frequency	I_C=-1A ; V_{CE}=-10V		90		MHz

◆ **h_{FE} Classifications**

D	E	F
60-120	100-200	160-320

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PACKAGE OUTLINE

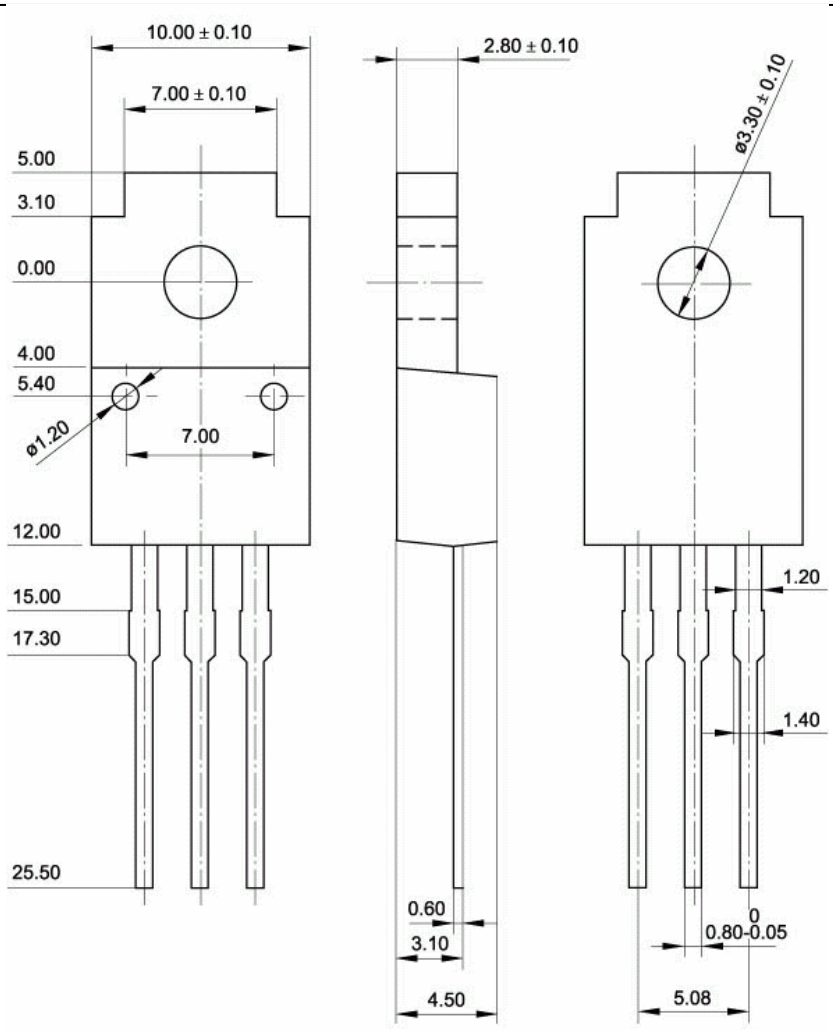


Fig.2 Outline dimensions (unindicated tolerance:±0.15 mm)